Functional Safety Information

LM5149-Q1

Functional Safety FIT Rate, FMD, and Pin FMA



Table of Contents

1 Overview	2
2 Functional Safety Failure In Time (FIT) Rates	
3 Failure Mode Distribution (FMD)	
4 Pin Failure Mode Analysis (Pin FMA)	

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1 Overview

This document contains information for LM5149-Q1 (VQFN package) to aid in a functional safety system design. Information provided are:

- Functional Safety Failure In Time (FIT) rates of the semiconductor component estimated by the application of industry reliability standards
- · Component failure modes and their distribution (FMD) based on the primary function of the device
- Pin failure mode analysis (Pin FMA)

Figure 1-1 shows the device functional block diagram for reference.

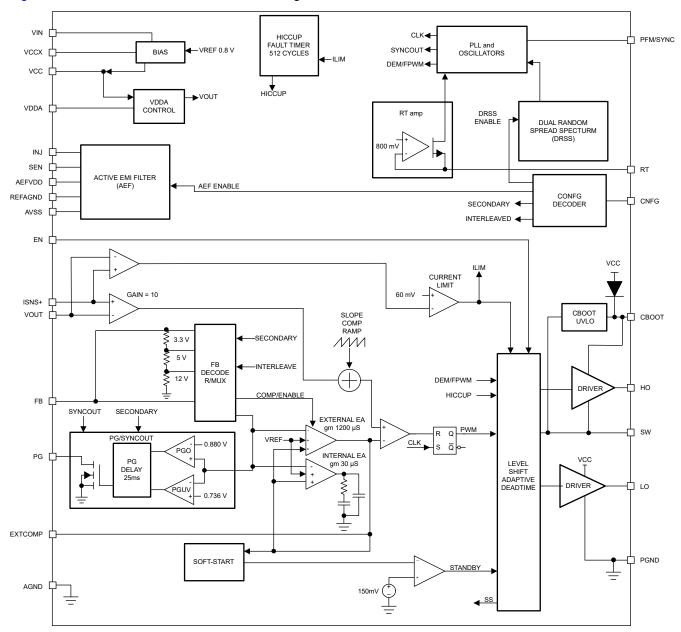


Figure 1-1. Functional Block Diagram

LM5149-Q1 was developed using a quality-managed development process, but was not developed in accordance with the IEC 61508 or ISO 26262 standards.



2 Functional Safety Failure In Time (FIT) Rates

This section provides Functional Safety Failure In Time (FIT) rates for LM5149-Q1 based on two different industry-wide used reliability standards:

- Table 2-1 provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- Table 2-2 provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-1. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

FIT IEC TR 62380 / ISO 26262	FIT (Failures Per 10 ⁹ Hours)
Total Component FIT Rate	16
Die FIT Rate	6
Package FIT Rate	10

The failure rate and mission profile information in Table 2-1 comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

Mission Profile: Motor Control from Table 11

Power dissipation: 750 mW

Climate type: World-wide Table 8Package factor (lambda 3): Table 17b

Substrate Material: FR4EOS FIT rate assumed: 0 FIT

Table 2-2. Component Failure Rates per Siemens Norm SN 29500-2

Table	Category	Reference FIT Rate	Reference Virtual T _J
5	CMOS, BICMOS ASICs Analog & mixed HV > 50-V supply	30 FIT	75°C

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in Table 2-2 come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.



3 Failure Mode Distribution (FMD)

The failure mode distribution estimation for LM5149-Q1 in Table 3-1 comes from the combination of common failure modes listed in standards such as IEC 61508 and ISO 26262, the ratio of sub-circuit function size and complexity and from best engineering judgment.

The failure modes listed in this section reflect random failure events and do not include failures due to misuse or overstress.

Table 3-1. Die Failure Modes and Distribution

Die Failure Modes	Failure Mode Distribution (%)
No Output Voltage	60%
Output not in specification – voltage or timing	25%
Gate driver stuck on	5%
Power Good - False trip or fails to trip	5%
Short circuit any two pins	5%



4 Pin Failure Mode Analysis (Pin FMA)

This section provides a Failure Mode Analysis (FMA) for the pins of the LM5149-Q1. The failure modes covered in this document include the typical pin-by-pin failure scenarios:

- Pin short-circuited to Ground (see Table 4-2)
- Pin open-circuited (see Table 4-3)
- Pin short-circuited to an adjacent pin (see Table 4-4)
- Pin short-circuited to supply (see Table 4-5)

Table 4-2 through Table 4-5 also indicate how these pin conditions can affect the device as per the failure effects classification in Table 4-1.

Table 4-1	ΤI	Classification	of Failure	Effects

Class	Failure Effects
Α	Potential device damage that affects functionality
В	No device damage, but loss of functionality
С	No device damage, but performance degradation
D	No device damage, no impact to functionality or performance

Figure 4-1 shows the LM5149-Q1 pin diagram. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the LM5149-Q1 data sheet.

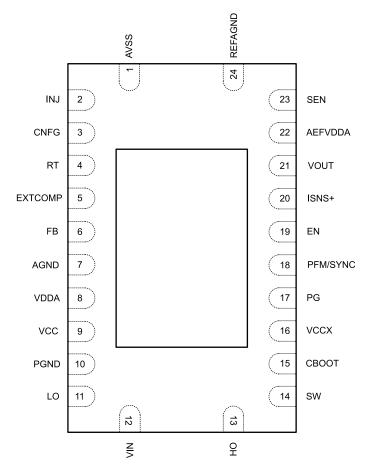


Figure 4-1. Pin Diagram

Following are the assumptions of use and the device configuration assumed for the pin FMA in this section:

- Application Circuit as per the LM5149-Q1 data sheet is used
 - PG is pulled up to VOUT



Table 4-2. Pin FMA for Device Pins Short-Circuited to Ground

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
AVSS	1	AVSS is ground. VOUT = expected VOUT	D
INJ	2	Active EMI filtering will not work but the regulator will continue regulating. VOUT = expected VOUT	С
CNFG	3	Active EMI filtering will be disabled. VOUT unaffected	С
RT	4	VOUT will attempt to regulate at maximum f _{SW} , causing maximum power disippation.	В
EXTCOMP	5	VOUT = 0 V	В
FB	6	Internal FB mode, VOUT = expected VOUT	D
ГБ	0	External FB mode, VOUT = VIN	А
AGND	7	AGND is GND. VOUT = expected VOUT	D
VDDA	8	VOUT = 0 V, no switching, loaded VCC output	В
VCC	9	VOUT = 0 V, no switching, loaded VCC output	В
PGND	10	PGND is GND. VOUT = expected VOUT	D
LO	11	VOUT = 0 V,VCC regulator loaded to the current limit	В
VIN	12	VOUT = 0 V	В
НО	13	VOUT = 0 V, VCC regulator loaded to the current limit	В
SW	14	VOUT = 0 V. High-side FET is shorted from VIN to GND.	А
CBOOT	15	VOUT = 0, VCC regulator loaded to the current limit	В
VCCX	16	VOUT = expected VOUT. The internal VCC regulator provides bias voltage.	С
		If in single phase, PG has no effect on operation. VOUT = expected VOUT	С
PG	17	If in interleaved primary mode, the secondary will detect no clock input and will shut down. Secondary phase is disabled and primary phase can current limit.	В
PFM/SYNC	18	VOUT = expected VOUT. No synchronization will be available and the LM5149-Q1 will be in FPWM mode.	С
EN	19	VOUT = 0 V. The LM5149-Q1 enters shutdown.	С
ISNS+	20	VOUT = 0 V; HO damaged	А
VOUT	21	VOUT = 0 V. Current limit reached, Hiccup mode occurs.	В
AEFVDDA	22	AEFVDDA = VCC. VCC is shorted and VOUT = 0 V. VCC loaded	В
SEN	23	Active EMI filtering will not work but the regulator will continue regulating. VOUT = expected VOUT	В
REFAGND	24	REFAGND is ground. VOUT = expected VOUT	D

Table 4-3. Pin FMA for Device Pins Open-Circuited

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
AVSS	1	Active EMI filtering will not work but the regulator will continue regulating. VOUT = expected VOUT	С
INJ	2	Active EMI filtering will not work but the regulator will continue regulating. VOUT = expected VOUT	С
CNFG	3	VOUT will continue operating normally. CNFG is used during start-up and enables AEF.	С
RT	4	RT will regulate to 500 mV, but the internal oscillator will not function.	В
EXTCOMP	5	VOUT will oscillate. If VOUT oscillates to VIN, damage can occur if VIN > 60 V.	А
FB	6	Internal FB mode, VOUT = expected VOUT	D
		External FB mode, VOUT = VIN	А
AGND	7	VOUT is indeterminate.	В
VDDA	8	Poor noise immunity	С
VCC	9	VOUT = 0 V	В
PGND	10	VOUT = 0 V	В



Table 4-3. Pin FMA for Device Pins Open-Circuited (continued)

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
LO	11	VOUT = expected VOUT with reduced efficiency	С
VIN	12	VOUT = 0 V	С
НО	13	If HO is opened while HO to SW has voltage, the high-side FET will never turn off. VOUT = VIN	Α
SW	14	VOUT is indeterminate. The CBOOT floating rail has no reference to the actual SW node. VOUT = VIN	А
CBOOT	15	VOUT = 0 V	В
VCCX	16	VCCX is held to ground by a weak pulldown. VOUT = expected VOUT	D
PG	17	If in single phase, PG has no effect on operation. VOUT = expected VOUT	С
		If in interleaved primary mode, the secondary will detect no clock input and will shut down. The secondary phase is disabled and primary phase can current limit.	В
PFM/SYNC	18	VOUT = expected VOUT	D
EN	19	VOUT = expected VOUT	D
ISNS+	20	The OPEN ISNS+ pin will block current limit and cause VOUT oscillations.	Α
VOUT	21	VOUT = 0 V	В
AEFVDDA	22	Active EMI filtering will not function.	С
SEN	23	Active EMI filtering will not function.	С
REFAGND	24	Active EMI filtering will not function.	С

Table 4-4. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

Pin Name	Pin No.	Shorted to	Description of Potential Failure Effect(s)	Failure Effect Class
AVSS	1	INJ	Active EMI filtering will not function. VOUT = expected VOUT	С
INJ	2	CNFG	Active EMI filtering will not function. VOUT = expected VOUT	С
CNFG	3	RT	VOUT = expected VOUT with erractic switching	В
RT	4	EXTCOMP	COMP cannot regulate down due to clamping by the internal RT.	В
EXTCOMP	5	FB	External FB Mode: COMP will regulate to .8 V and the output will be unregulated. VOUT = any voltage	В
			Internal FB Mode: COMP will rise up to VDD. VOUT = VIN	Α
	_	ACNID	External FB Mode: VOUT = VIN	Α
FR	FB 6	AGND	Internal FB Mode: VOUT = expected VOUT	D
AGND	7	VDDA	VDDA will be grounded. VOUT = 0 V	В
VDDA	8	VCC	VOUT = expected VOUT	D
VCC	9	PGND	VCC will be grounded. VOUT = 0 V	В
PGND	10	LO	VOUT = 0 V. VCC is loaded by LO driver.	В
LO	11	VIN	VOUT = 0 V. The driver will be damaged if VIN > 6.5 V.	Α
VIN	12	НО	VOUT = VIN	Α
НО	13	SW	VOUT = 0 V	В
SW	14	CBOOT	VOUT = 0 V	В
СВООТ	15	VCCX	VOUT < 5 V	Α
VCCX	16	PG	PG pulldown can damage. VOUT = expected VOUT	Α
PG	17	PFM/SYNC	VOUT = expected VOUT	С
PFM/SYNC	18	EN	VOUT = expected VOUT	Α
EN	19	ISNS+	EN is high voltage rated. VOUT = expected VOUT if VOUT > 1 V. If VOUT < 1 V, the device is disabled.	В
ISNS+	20	VOUT	Current limit is disabled since the current limit resistor would be shorted. VOUT cannot regulate since current mode feedback is shorted.	Α



Table 4-4. Pin FMA for Device Pins Short-Circuited to Adjacent Pin (continued)

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Pin Name	Pin No.	Shorted to	Description of Potential Failure Effect(s)	Failure Effect Class
VOUT	21	AEFVDDA	Active EMI filtering will not function and damage will occur if VOUT > 6.5 V. VOUT = expected VOUT	А
AEFVDDA	22	SEN	Active EMI filtering will not function. VOUT = expected VOUT	С
SEN	23	REFAGND	Active EMI filtering will not function. VOUT = expected VOUT	С
REFAGND	24	AVSS	No impact	D

Table 4-5. Pin FMA for Device Pins Short-Circuited to VIN

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
AVSS	1	Active EMI filtering will not function, high VIN current	Α
INJ	2	Active EMI filtering will not function, high VIN current	Α
CNFG	3	VOUT = VIN	Α
RT	4	VOUT = 0 V; High VIN current	Α
EXTCOMP	5	This will bring VDDA up to VIN. VOUT = VIN.	Α
FB	6	This will bring VDDA up to VIN. VOUT = VIN	Α
AGND	7	VOUT = VIN; High VIN current	Α
VDDA	8	If VIN < 6.5 V, VOUT = expected VOUT	D
VDDA	0	If VIN > 6.5 V, exceeds maximum ratings and VDDA is damaged.	Α
VCC	9	If VIN < 6.5 V, VOUT = expected VOUT	D
VCC	9	If VIN > 6.5 V, exceeds maximum ratings and VCC is damaged.	Α
PGND	10	VOUT = VIN; High VIN current	Α
10	11	For VIN < 6.5 V, VOUT = 0; excess current from VIN	В
LO	11	For VIN > 6.5 V, exceeds maximum ratings and pin LO is damaged.	Α
VIN	12	N/A	D
НО	12	For VIN < 6.5 V, VOUT = dropout lower than VIN, no switching, excess current from VIN	В
но	13	For VIN > 6.5 V, exceeds maximum ratings and HO is damaged, VOUT = VIN	Α
SW	14	VOUT = VIN, excess current from VIN. LO turns on and shorts against VIN.	
		For VIN < 6.5 V, VOUT = expected VOUT, erratic switching	В
CBOOT	15	For VIN > 6.5 V, exceeds maximum ratings and the CBOOT pin is damaged, HO damaged. VOUT = VIN	Α
VCCV	16	If VCCX = VOUT, for VIN < 6.5 V, VOUT = VIN	В
VCCX	16	For VIN > 6.5 V, exceeds maximum ratings and VCCX is damaged.	Α
PG	17	For VIN < 6.5 V, VOUT = expected VOUT, PG forced high	В
PG	17	For VIN > 6.5 V, exceeds maximum ratings and PG is destroyed.	Α
		If PFM = GND, VOUT = 0 V, excess current from VIN	В
PFM/SYNC	18	If PFM = VDDA and VIN < 6.5 V, VOUT = expected VOUT and erratic switching.	В
		If VIN > 6.5 V, exceeds maximum ratings and PFM is damaged. VOUT = expected VOUT	Α
EN	19	The part will be always on. VOUT = expected VOUT	С
ICNIC	20	If VIN < 60 V, VOUT = VIN	В
ISNS+	20	If VIN > 60 V, exceeds maximum ratings and CS is damaged.	Α
VOLIT	21	If VIN < 60 V, VOUT = VIN	В
VOUT	21	If VIN > 60 V, exceeds maximum ratings and CS is damaged.	Α
AEFVDDA	22	Active EMI filtering will not function, high VIN current	Α
SEN	23	Active EMI filtering will not function, high VIN current	Α
REFAGND	24	Active EMI filtering will not function, high VIN current	Α

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